

Silicon PNP Power Transistors

2SB566 2SB566A

DESCRIPTION

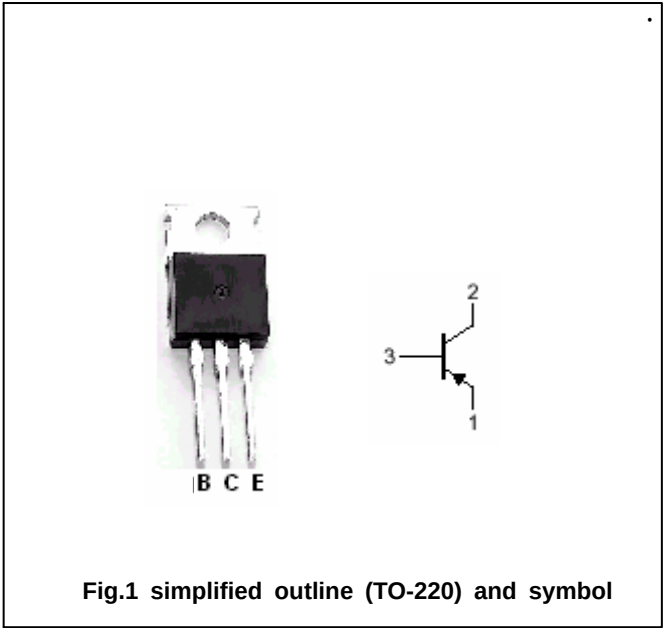
- With TO-220C package
- Complement to type 2SD476/476A

APPLICATIONS

- For low frequency power amplifier
power switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage		Open emitter	-70	V
V _{CEO}	Collector-emitter voltage	2SB566	Open base	-50	V
		2SB566A		-60	
V _{EBO}	Emitter-base voltage		Open collector	-5	V
I _C	Collector current			-4	A
I _{CM}	Collector current-peak			-8	A
P _C	Collector power dissipation		T _C =25°C	40	W
T _j	Junction temperature			150	°C
T _{stg}	Storage temperature			-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage		I _C =-10 μA ; I _E =0	-70			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB566	I _C =-50mA; R _{BE} =∞	-50			V
		2SB566A		-60			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-10 μA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-2 A; I _B =-0.2 A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-2 A; I _B =-0.2 A			-1.2	V
I _{CBO}	Collector cut-off current		V _{CB} =-50V; I _E =0			-1	μA
h _{FE-1}	DC current gain		I _C =-0.1A ; V _{CE} =-4V	35			
h _{FE-2}	DC current gain		I _C =-1A ; V _{CE} =-4V	60		200	
f _T	Transition frequency		I _C =-0.5A ; V _{CE} =-4V		15		MHz

Switching times

t _{on}	Turn-on time	I _C =-0.5A ; V _{CC} =-10.5V I _{B1} =-I _{B2} =-0.05 A		0.3		μs
t _{off}	Turn-off time			3.0		μs
t _{stg}	Storage time			2.5		μs

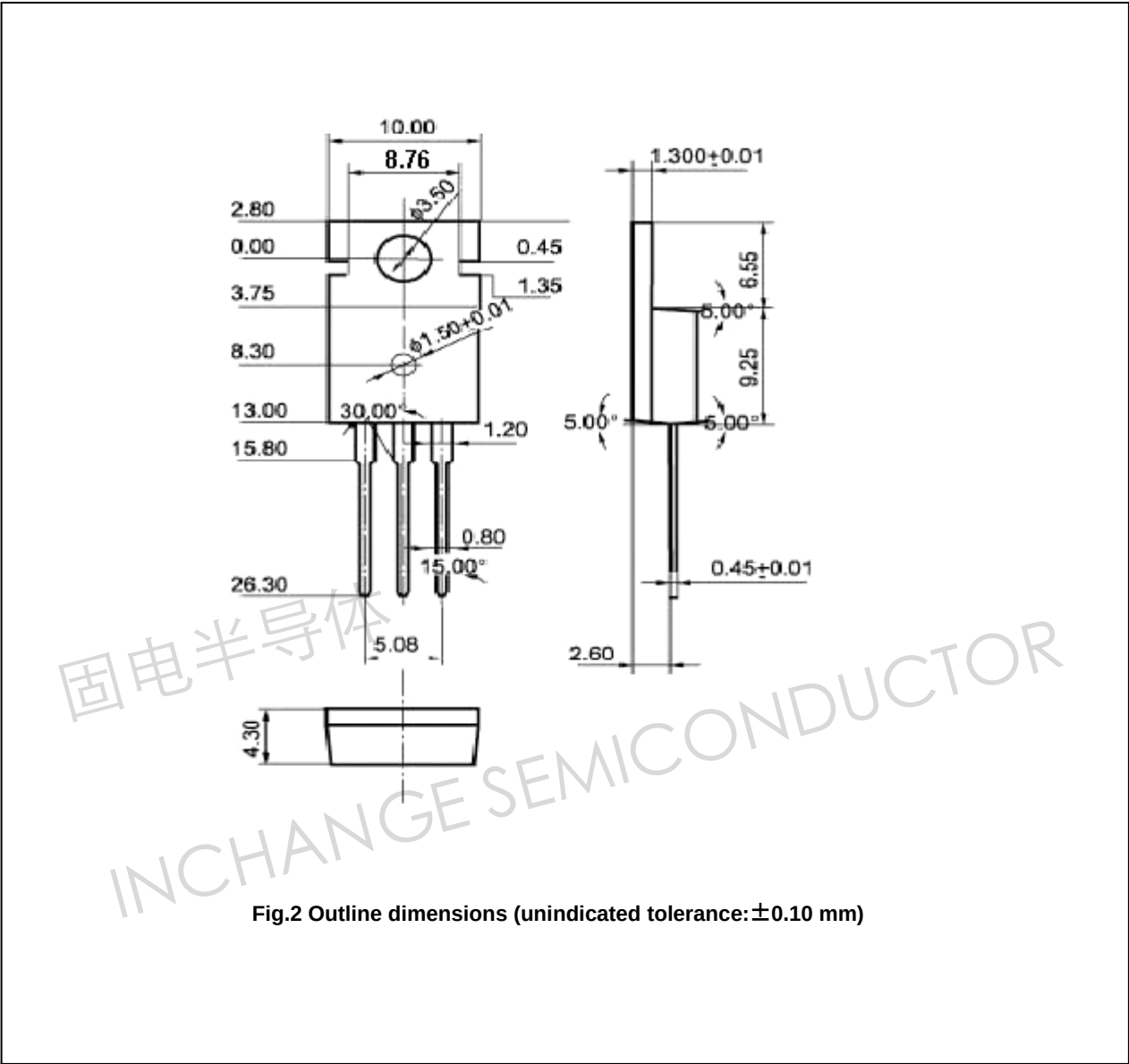
◆ h_{FE-2} classifications

B	C
60-120	100-200

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PACKAGE OUTLINE



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